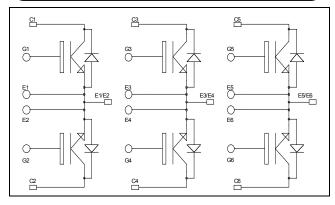


## Triple Dual Common Source Trench + Field Stop IGBT3 Power Module



# APTGT100TDU60PG

## $V_{CES} = 600V$ $I_{C} = 100A$ @ Tc = 80°C

#### Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
    - Lead frames for power connections
- High level of integration

### Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS Compliant

#### Absolute maximum ratings

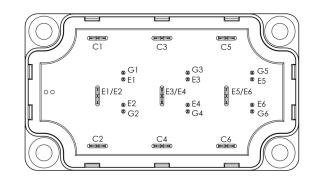
|                | Symbol                       | Parameter                             |                      | Max ratings | Unit |  |
|----------------|------------------------------|---------------------------------------|----------------------|-------------|------|--|
|                | V <sub>CES</sub>             | Collector - Emitter Breakdown Voltage |                      | 600         | V    |  |
| I <sub>C</sub> | т                            | Continuous Collector Current          | $T_C = 25^{\circ}C$  | 150         |      |  |
|                | Continuous Collector Current | $T_C = 80^{\circ}C$                   | 100                  | А           |      |  |
|                | I <sub>CM</sub>              | Pulsed Collector Current              | $T_C = 25^{\circ}C$  | 200         |      |  |
|                | V <sub>GE</sub>              | Gate – Emitter Voltage                |                      | ±20         | V    |  |
|                | P <sub>D</sub>               | Maximum Power Dissipation             | $T_C = 25^{\circ}C$  | 340         | W    |  |
|                | RBSOA                        | Reverse Bias Safe Operating Area      | $T_j = 150^{\circ}C$ | 200A @ 550V |      |  |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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# APTGT100TDU60PG - Rev 2 October 2012

1 - 6





#### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

#### **Electrical Characteristics**

| Symbol               | Characteristic                       | Test Conditions                         |                        | Min | Тур | Max | Unit |
|----------------------|--------------------------------------|---|------------------------|-----|-----|-----|------|
| I <sub>CES</sub>     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 600V$            |                        |     |     | 250 | μA   |
| V                    | Collector Emitter Saturation Voltage | $V_{GE} = 15V$ $I_{C} = 100A$           | $T_j = 25^{\circ}C$    |     | 1.5 | 1.9 | V    |
| V <sub>CE(sat)</sub> | Conector Ennitier Saturation Voltage |   | $T_{j} = 150^{\circ}C$ |     | 1.7 |     | v    |
| V <sub>GE(th)</sub>  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$ |                        | 5.0 | 5.8 | 6.5 | V    |
| I <sub>GES</sub>     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$             |                        |     |     | 400 | nA   |

#### **Dynamic Characteristics**

| Symbol              | Characteristic               | Test Conditions  |   | Тур   | Max | Unit |
|---------------------|------------------------------|--|---|-------|-----|------|
| Cies                | Input Capacitance            | $V_{GE} = 0V$  |   | 6100  |     |      |
| Coes                | Output Capacitance           | $V_{CE} = 25V$   |   | 390   |     | pF   |
| Cres                | Reverse Transfer Capacitance | f = 1 MHz  |   | 190   |     |      |
| T <sub>d(on)</sub>  | Turn-on Delay Time           | Inductive Switching (25°C)                                 |   | 115   |     |      |
| Tr                  | Rise Time                    | $V_{GE} = \pm 15V$   |   | 45    |     | ns   |
| T <sub>d(off)</sub> | Turn-off Delay Time          | $V_{Bus} = 300V$<br>$I_{C} = 100A$                         |   | 225   |     |      |
| $T_{\rm f}$         | Fall Time                    | $R_G = 3.3\Omega$  |   | 55    |     |      |
| T <sub>d(on)</sub>  | Turn-on Delay Time           | Inductive Switching (150°C                                 | ) | 130   |     |      |
| Tr                  | Rise Time                    | $V_{GE} = \pm 15V$   |   | 50    |     |      |
| T <sub>d(off)</sub> | Turn-off Delay Time          | $V_{Bus} = 300V$<br>$I_{C} = 100A$                         |   | 300   |     | ns   |
| $T_{\rm f}$         | Fall Time                    | $R_G = 3.3\Omega$  |   | 70    |     |      |
| Б                   |                              | $V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$                     |   | 0.4   |     | In I |
| Eon                 | Turn on Energy               | $V_{Bus} = 300V$ $T_j = 150^{\circ}C$                      |   | 0.875 |     | mJ   |
| Б                   | Turn off Energy              | $I_{\rm C} = 100 {\rm A}$ $T_{\rm j} = 25^{\circ} {\rm C}$ |   | 2.5   |     | mJ   |
| E <sub>off</sub>    | Turn off Energy              | $R_G = 3.3\Omega \qquad T_j = 150^{\circ}C$                |   | 3.5   |     | 111J |

#### **Reverse diode ratings and characteristics**

| Symbol           | Characteristic                          | Test Conditions                                    |  | Min | Тур | Max        | Unit |
|------------------|---|--|--|-----|-----|------------|------|
| V <sub>RRM</sub> | Maximum Peak Repetitive Reverse Voltage |  |  | 600 |     |            | V    |
| I <sub>RM</sub>  | Maximum Reverse Leakage Current         | V <sub>R</sub> =600V                               | $T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$ |     |     | 250<br>500 | μΑ   |
| I <sub>F</sub>   | DC Forward Current                      |  | $Tc = 80^{\circ}C$                       |     | 100 |            | А    |
| V                | Diode Forward Voltage                   | $I_{\rm F} = 100 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$ | $T_i = 25^{\circ}C$                      |     | 1.6 | 2          | V    |
| $V_{\rm F}$      |   |  | $T_{i} = 150^{\circ}C$                   |     | 1.5 |            | v    |
| t                | Reverse Recovery Time                   |  | $T_j = 25^{\circ}C$                      |     | 125 |            | ns   |
| t <sub>rr</sub>  | Reverse Recovery Time                   |  | $T_{j} = 150^{\circ}C$                   |     | 220 |            | 115  |
| 0                | Reverse Recovery Charge                 | $I_{\rm F} = 100 {\rm A}$                          | $T_j = 25^{\circ}C$                      |     | 4.7 |            | лС   |
| Q <sub>rr</sub>  | Reverse Recovery Charge                 | $V_{\rm R} = 300 V$<br>di/dt = 2000 A/µs           | $T_{j} = 150^{\circ}C$                   |     | 9.9 |            | μC   |
| Б                | Devence Deservery Energy                |  | $T_j = 25^{\circ}C$                      |     | 1.1 |            | m I  |
| Er               | Reverse Recovery Energy                 |  | $T_{i} = 150^{\circ}C$                   |     | 2.4 |            | mJ   |

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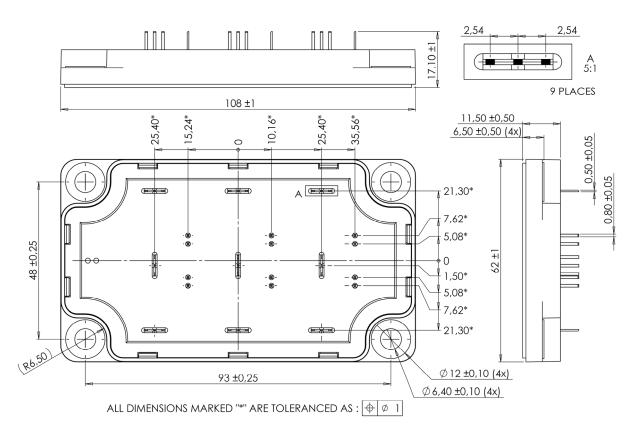


# APTGT100TDU60PG

#### Thermal and package characteristics

| Symbol            | Characteristic  |             |       | Min  | Тур | Max  | Unit |
|-------------------|---|-------------|-------|------|-----|------|------|
| р                 | Junction to Case Thermal Resistance                           |             | IGBT  |      |     | 0.44 | °C/W |
| R <sub>thJC</sub> |   |             | Diode |      |     | 0.77 |      |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |             |       | 4000 |     |      | V    |
| T <sub>J</sub>    | Operating junction temperature range                          |             |       | -40  |     | 175  |      |
| T <sub>STG</sub>  | Storage Temperature Range                                     |             |       | -40  |     | 125  | °C   |
| T <sub>C</sub>    | Operating Case Temperature                                    |             |       | -40  |     | 100  |      |
| Torque            | Mounting torque   | To heatsink | M6    | 3    |     | 5    | N.m  |
| Wt                | Package Weight  |             |       |      |     | 250  | g    |

SP6-P Package outline (dimensions in mm)



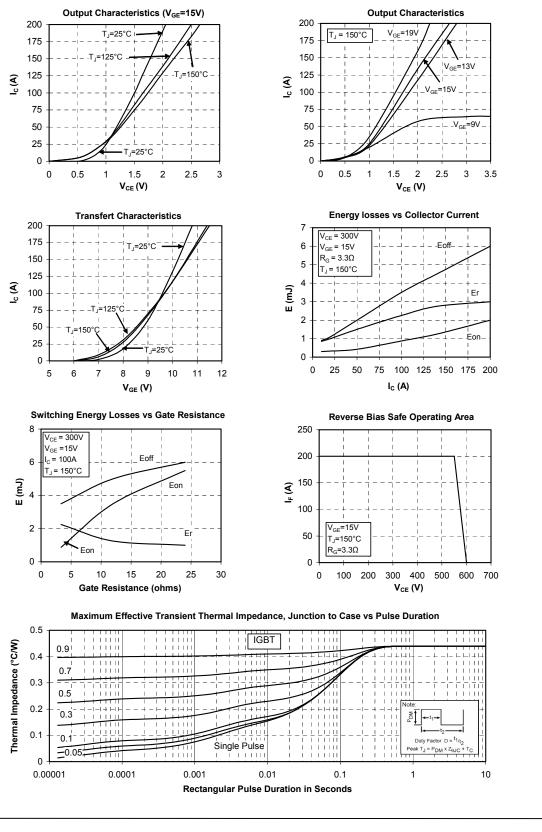
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

3 - 6

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#### **Typical Performance Curve**



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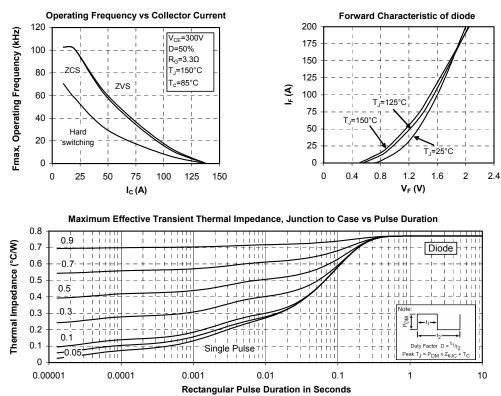
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4 - 6

APTGT100TDU60PG-Rev 2 October 2012



# APTGT100TDU60PG



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5 - 6



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6 - 6

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